

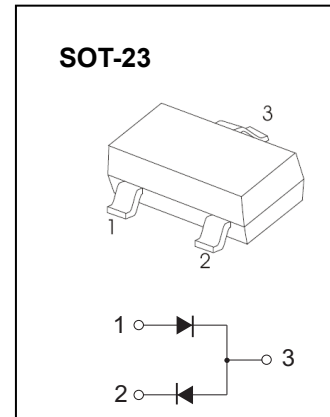


SOT-23 Plastic-Encapsulate Diodes

1SS226 SWITCHING DIODE

FEATURES

- Low forward voltage
- Fast reverse recovery time
- Small total capacitance



MARKING: C3

Maximum Ratings ,Single Diode @Ta=25°C

| Parameter | Symbol | Limit | Unit |
|--------------------------------------|-----------|----------|------|
| Non-Repetitive Peak Reverse Voltage | V_{RM} | 85 | V |
| Peak Repetitive Peak Reverse Voltage | V_{RRM} | 80 | V |
| Working Peak Reverse Voltage | V_{RWM} | | |
| DC Blocking Voltage | V_R | | |
| Forward Continuous Current | I_{FM} | 300 | mA |
| Average Rectified Output Current | I_O | 100 | mA |
| Peak Forward Surge Current @t=10ms | I_{FSM} | 2 | A |
| Power Dissipation | P_D | 150 | mW |
| Junction Temperature | T_J | 150 | °C |
| Storage Temperature | T_{STG} | -55~+150 | °C |

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

| Parameter | Symbol | Test conditions | Min | Max | Unit |
|---------------------------------|------------|------------------|-----|-----|---------|
| Reverse breakdown voltage | $V_{(BR)}$ | $I_R=100\mu A$ | 80 | | V |
| Reverse voltage leakage current | I_R | $V_R=80V$ | | 0.5 | μA |
| Forward voltage | V_F | $I_F=100mA$ | | 1.2 | V |
| Diode capacitance | C_D | $V_R=0V, f=1MHz$ | | 3 | pF |
| Reverse recovery time | t_{rr} | $I_F=10mA$ | | 4 | ns |

Typical Characteristics

1SS226

